N-Channel 60-V (D-S) MOSFET

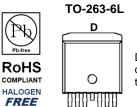
Key Features:

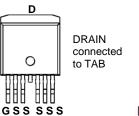
- Low r_{DS(on)} trench technology
- · Low thermal impedance
- · Fast switching speed

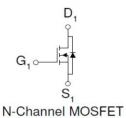
Typical	Application	ons:
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- · White LED boost converters
- Automotive Systems
- Industrial DC/DC Conversion Circuits

PRODUCT SUMMARY			
V _{DS} (V)	$r_{DS(on)}(m\Omega)$	I□ (A)	
60	$2.5 @ V_{GS} = 10V$	200 ^a	
00	$3.9 @ V_{GS} = 5.5V$	200	







ABSOLUTE MAXIMUM RATINGS ($T_A = 25^{\circ}$ C UNLESS OTHERWISE NOTED)					
Parameter		Symbol	Limit	Units	
Drain-Source Voltage		V_{DS}	60	V	
Gate-Source Voltage		V_{GS}	±20	V	
Continuous Drain Current a	T _C =25°C	I _D	200	Α	
Pulsed Drain Current ^b		I _{DM}	800	Υ	
Continuous Source Current (Diode Conduction) a	T _C =25°C	I _S	90	Α	
Power Dissipation ^a	T _C =25°C	P_{D}	300	W	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to 175	°C	

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Maximum	Units		
Maximum Junction-to-Ambient °	$R_{\theta JA}$	62.5	°C/W		
Maximum Junction-to-Case	$R_{\theta JC}$	0.5	C/VV		

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Notes

- a. Package Limited
- b. Pulse width limited by maximum junction temperature
- c. Surface Mounted on 1" x 1" FR4 Board.

Electrical Characteristics

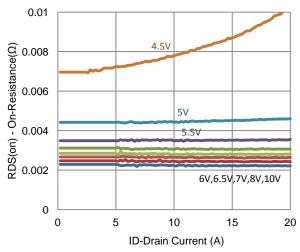
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
Static						
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = 250 \text{ uA}$				V
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±100	nA
Zero Gate Voltage Drain Current	lana	$V_{DS} = 48 \text{ V}, V_{GS} = 0 \text{ V}$			1	uA
Zero Gate Voltage Brain Gurrent	I _{DSS}	$V_{DS} = 48 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			10	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	250			Α
Drain-Source On-Resistance ^a	r	$V_{GS} = 10 \text{ V}, I_{D} = 40 \text{ A}$			2.5	mΩ
Drain-Source On-Resistance	r _{DS(on)}	$V_{GS} = 5.5 \text{ V}, I_D = 32 \text{ A}$			3.9	11152
Forward Transconductance ^a	g _{fs}	$V_{DS} = 30 \text{ V}, I_{D} = 40 \text{ A}$		103		S
Diode Forward Voltage ^a	V_{SD}	$I_{S} = 45 \text{ A}, V_{GS} = 0 \text{ V}$		0.85		V
		Dynamic ^b				
Total Gate Charge	Q_g	$V_{DS} = 30 \text{ V}, V_{GS} = 5.5 \text{ V},$		76		
Gate-Source Charge	Q_{gs}	$I_{DS} = 30 \text{ V}, V_{GS} = 3.3 \text{ V},$ $I_{D} = 2 \text{ A}$		16		nC
Gate-Drain Charge	Q_gd	10 - 2 A		50		
Turn-On Delay Time	t _{d(on)}	$V_{DS} = 30 \text{ V}, R_1 = 15 \Omega,$		35		
Rise Time	t _r	$V_{DS} = 30 \text{ V}, R_L - 13 \Omega,$ $I_D = 2 \text{ A},$		74		ne
Turn-Off Delay Time	$t_{d(off)}$	$V_{GEN} = 10 \text{ V}, R_{GEN} = 6 \Omega$		99		ns
Fall Time	t _f	V GEN = 10 V, 1 (GEN = 0.22		153		
Input Capacitance	C _{iss}	_		4839		
Output Capacitance	C _{oss}	$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ Mhz}$		3302		pF
Reverse Transfer Capacitance	C_{rss}			919		

Notes

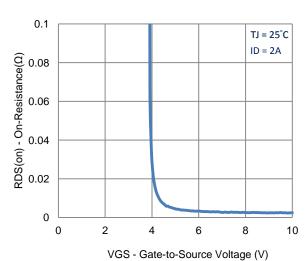
- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

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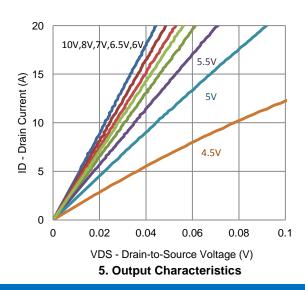
Typical Electrical Characteristics



1. On-Resistance vs. Drain Current



3. On-Resistance vs. Gate-to-Source Voltage

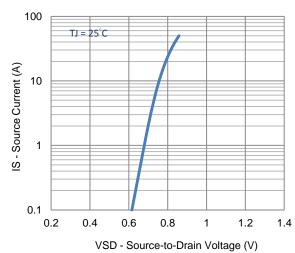


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TJ = 25°C

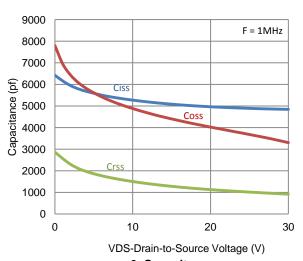
(Y) tuend 10
UELD 10
0 1 2 3 4 5 6

VGS - Gate-to-Source Voltage (V)

2. Transfer Characteristics

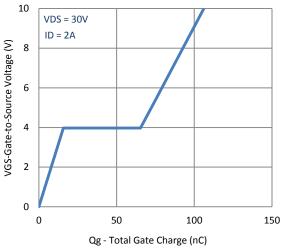


4. Drain-to-Source Forward Voltage

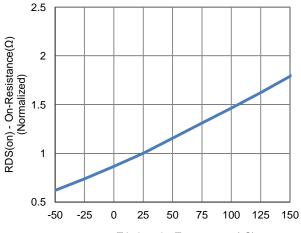


6. Capacitance

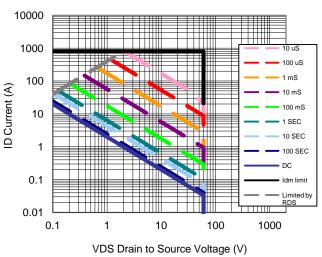
Typical Electrical Characteristics



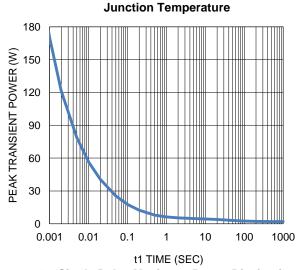
7. Gate Charge



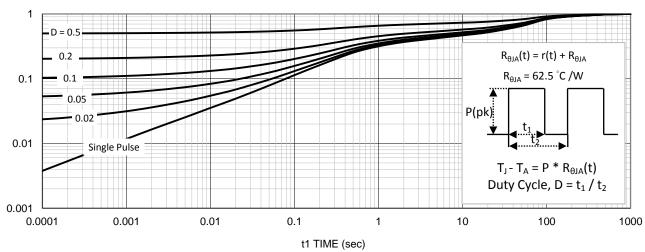
TJ -JunctionTemperature(°C)
8. Normalized On-Resistance Vs



9. Safe Operating Area

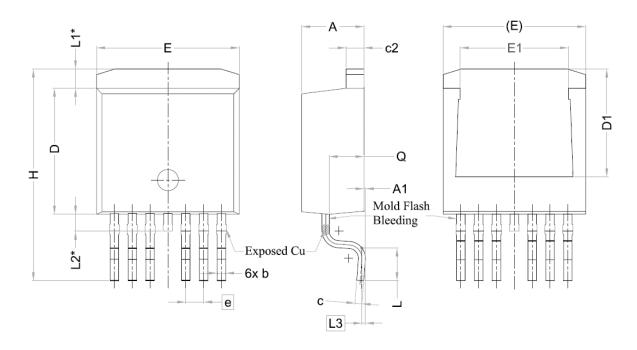


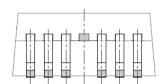
10. Single Pulse Maximum Power Dissipation



11. Normalized Thermal Transient Junction to Ambient

Package Information





SYMBOL		DIMENSIONS	6	
STWIDOL	MIN.	NOM.	MAX.	
А	4.24	4.44	4.64	
A1	0.00	0.10	0.25	
b	0.50	0.60	0.70	
С	0.40	0.50	0.60	
c2	1.15	1.27	1.40	
D	8.82	8.92	9.02	
D1	6.86	7.65	_	
E	9.96	10.16	10.36	
E1	6.89	7.77	7.89	
е	1.27 BSC			
Н	14,61	15,00	15,88	
L	1.78	2.32	2.79	
L1	1.36 REF.			
L2	1,20 REF.			
L3	0.25 BSC			
Q	2.30	2.48	2.70	